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U.S. UTILITY Patent Application

PATENT NUMBER and  
ISSUE DATE

APPL NUM 10034163	FILING DATE 12/27/2001	CLASS 438	SUBCLASS 3	GAU 2812	EXAMINER S. FOONG
<b>**APPLICANTS:</b> Jeon Joong; 2823					
<b>**CONTINUING DATA VERIFIED:</b>					
<b>** FOREIGN APPLICATIONS VERIFIED:</b>					
PG-PUB <input type="checkbox"/>		DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>	
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no 35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no Verified and Acknowledged Examiners's initials				ATTORNEY DOCKET NO G0518	
TITLE : Preparation of stack high-K gate dielectrics with nitrided layer					

U.S. DEPT. OF COMM./PAT. & TM.-PTO-436L (Rev. 12-94)

<b>NOTICE OF ALLOWANCE MAILED</b>		<b>CLAIMS ALLOWED</b>	
		Total Claims: <input type="checkbox"/> Print Claim for O.G. <input type="checkbox"/>	
<b>ISSUE FEE</b>		<b>DRAWING</b>	
Amount Due	Date Paid	Sheets Drwg.	Figs. Drwg.
		Print Fig.	
<input type="checkbox"/> <b>TERMINAL DISCLAIMER</b>		Application Examiner	
		<b>PREPARED FOR ISSUE</b>	
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